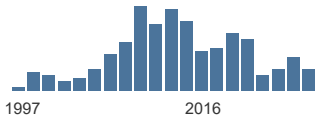
Citation report for 247 results from Web of Science Core Collection between 1900 and 2018 Go

You searched for: **Article Group for:** De Meyer, K **...More**

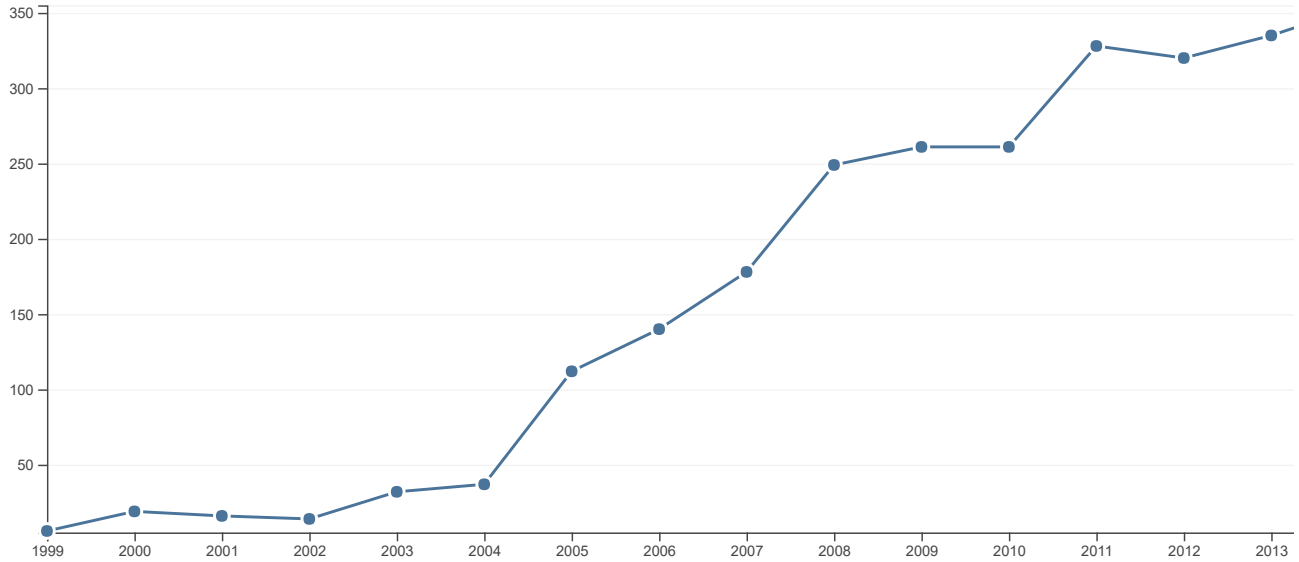
This report reflects citations to source items indexed within Web of Science Core Collection. Perform a Cited Reference Search to include citations to items not indexed within Web of Science Core Collection.

Export Data: Save to Text File

Total Publications	*h*-index	Sum of Times Cited	Citing articles
247	29	3,443	2,807
Average citations per item		Without self citations	Without self citations
13.94		3,225	2,684



Sum of Times Cited per Year



Sort by: Times Cited -- highest to lowest

Page 1 of 25

Use the checkboxes to remove individual items from this Citation Report

or restrict to items published between 1900 and 2018 Go

	2014	2015	2016	2017	2018	Total	Average Citations per Year
	354	282	327	172	0	3443	181.21
1. **Electrical Modeling and Characterization of Through Silicon via for Three-Dimensional ICs** By: Katti, Guruprasad; Stucchi, Michele; De Meyer, Kristin; et al. IEEE TRANSACTIONS ON ELECTRON DEVICES Volume: 57 Issue: 1 Pages: 256-262 Published: JAN 2010	38	42	41	16	0	260	32.50

2.	**Analysis of the parasitic S/D resistance in multiple-gate FETs** By: Dixit, A; Kottantharayil, A; Collaert, N; et al. IEEE TRANSACTIONS ON ELECTRON DEVICES Volume: 52 Issue: 6 Pages: 1132-1140 Published: JUN 2005	16	13	20	11	0	215	16.54
3.	**VARIOT: A novel multilayer tunnel barrier concept, for low-voltage nonvolatile memory devices** By: Govoreanu, B; Blomme, P; Rosmeulen, M; et al. IEEE ELECTRON DEVICE LETTERS Volume: 24 Issue: 2 Pages: 99-101 Published: FEB 2003	11	5	3	2	0	136	9.07
4.	**Influence of device engineering on the analog and RF performances of SOI MOSFETs** By: Kilchytska, V; Neve, A; Vancaillie, L; et al. IEEE TRANSACTIONS ON ELECTRON DEVICES Volume: 50 Issue: 3 Pages: 577-588 Published: MAR 2003	15	10	14	8	0	114	7.60
5.	**Direct and Indirect Band-to-Band Tunneling in Germanium-Based TFETs** By: Kao, Kuo-Hsing; Verhulst, Anne S.; Vandenberghe, William G.; et al. IEEE TRANSACTIONS ON ELECTRON DEVICES Volume: 59 Issue: 2 Pages: 292-301 Published: FEB 2012	20	24	24	16	0	110	18.33
6.	**Passivation of Ge(100)/GeO2/high-kappa gate stacks using thermal oxide treatments** By: Bellenger, F.; Houssa, M.; Delabie, A.; et al. JOURNAL OF THE ELECTROCHEMICAL SOCIETY Volume: 155 Issue: 2 Pages: G33-G38 Published: 2008	9	5	5	3	0	104	10.40
7.	**Record I-ON/I-OFF performance for 65nm Ge pMOSFET and novel Si passivation scheme for improved EOT scalability** By: Mitard, J.; De Jaeger, B.; Leys, F. E.; et al. Book Group Author(s): IEEE Conference: IEEE International Electron Devices Meeting Location: San Francisco, CA Date: DEC 15-17, 2008 Sponsor(s): IEEE Electron Devices Soc IEEE INTERNATIONAL ELECTRON DEVICES MEETING 2008, TECHNICAL DIGEST Book Series: International Electron Devices Meeting Pages: 873-+ Published: 2008	10	5	8	1	0	95	9.50
8.	**Impact of line-edge roughness on FinFET matching performance** By: Baravelli, Ernanuele; Dixit, Abhisek; Rooyackers, Rita; et al. IEEE TRANSACTIONS ON ELECTRON DEVICES Volume: 54 Issue: 9 Pages: 2466-2474 Published: SEP 2007	8	4	4	7	0	86	7.82
9.	**FinFET analogue characterization from DC to 110 GHz** By: Lederer, D; Kilchytska, V; Rudenko, T; et al. Conference: 1st EUROSOI Workshop Location: Granada, SPAIN Date: JAN 19-21, 2005 Sponsor(s): EUROSOI SOLID-STATE ELECTRONICS Volume: 49 Issue: 9 Pages: 1488-1496 Published: SEP 2005	6	3	4	0	0	71	5.46
10.	**Analysis of leakage currents and impact on off-state power consumption for CMOS technology in the 100-nm regime** By: Henson, WK; Yang, N; Kubicek, S; et al. IEEE TRANSACTIONS ON ELECTRON DEVICES Volume: 47 Issue: 7 Pages: 1393-1400 Published: JUL 2000	5	1	1	0	0	56	3.11

Select Page | Save to Text File

Sort by: Times Cited -- highest to lowest

Page 1 of 25

247 records matched your query of the 65,301,887 in the data limits you selected.